PNP TRANSISTOR **8550**

-1.5A

TO-92

- Power Dissipation: 1.0W
- Collector Current: -1.5A
- Collector-Base Voltage: -45V

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS（Ta=25℃）

PARAMETERS	SYMBOL	MIN	TYP	MAX	UNIT	CONDITION
Collector-Emitter Breakdown Voltage	BVceo	-25			V	Ic=-0.1mA
Collector-Base Breakdown Voltage	BVcbo	-45			V	Ic=-100*u*A
Emitter-Base Breakdown Voltage	BVebo	-5			V	Ie=-100μA
Collector-Base Leakage	Icbo			-0.1	*u*A	Vcb=-40V
Collector-Emitter Leakage	Iceo			-0.1	*u*A	Vce=-20V
Emitter-Base Leakage	Iebo			-0.1	*u*A	Veb=-5V
Collector-Emitter Saturation Voltage	Vce(sat)			-0.6	V	Ic=-1500mA, Ib=-50mA
Base-Emiiter Saturation Voltage	Vbe(sat)			-1.2	V	Ic=-1500mA, Ib=-50mA
DC Current Gain	Hfe1 Hfe2	85 50		300		Vce=-1V,Ic=-50mA Vce=-1V,Ic=-500mA
Collector Current	Ic			-0.5	A	
Peak Collector Current	Icp			-8	A(Pulse)	
Current Gain Bandwidth	f_T	150			MHz	Vcb=-6V, Ic=-20mA
Output Capacitance	Cob			32	pF	Vcb=-20V,Ie=0,f=1MHz
Power Dissipation	Pc			1.0	W	
Junction Temperature	Tj			150	℃	
Storage Temperature	Tstg	-55		150	℃	

Hfe1 Classification

Rank	B	C	D
Range	85-160	120-200	160-300

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